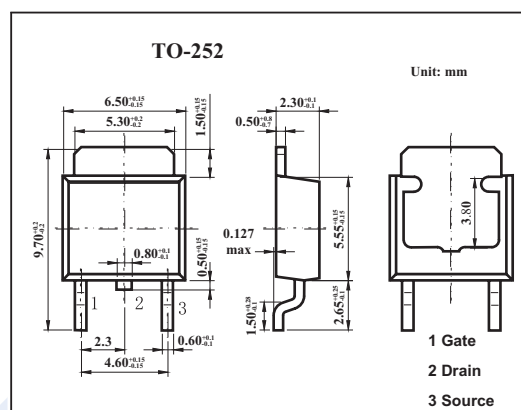
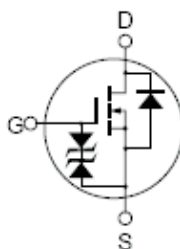


Silicon N-Channel MOSFET 2SK2796S

■ Features

- Low on-resistance
- $R_{DS} = 0.12 \Omega$ typ.
- High speed switching



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	60	V
Gate to source voltage	V_{GS}	± 20	V
Drain current	I_D	5	A
	I_{DP}^*	20	A
Power dissipation	P_D	20	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain source breakdown voltage	V_{DS}	$I_D = 10\text{mA}$, $V_{GS} = 0\text{V}$	60			V
Drain cut-off current	I_{DSS}	$V_{DS} = 60\text{V}$, $V_{GS} = 0$			10	μA
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16\text{V}$, $V_{DS} = 0$			± 10	μA
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	1.0		2.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$, $I_D = 3\text{A}$	2.5	4.0		S
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 3\text{A}$		0.12	0.16	Ω
		$V_{GS} = 4\text{V}$, $I_D = 3\text{A}$		0.16	0.25	Ω
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0$, $f = 1\text{MHz}$		180		pF
Output capacitance	C_{oss}			90		pF
Reverse transfer capacitance	C_{rss}			30		pF
Turn-on delay time	t_{on}	$I_D = 3\text{A}$, $V_{GS(on)} = 10\text{V}$, $R_L = 10 \Omega$		9		ns
Rise time	t_r			25		ns
Turn-off delay time	t_{off}			35		ns
Fall time	t_f			55		ns